

650 V, 50 mΩ Gallium Nitride (GaN) FET 20 March 2020

1. General description

The GAN063-650WSA is a 650 V, 50 m Ω Gallium Nitride (GaN) FET. It is a normally-off device that combines Nexperia's state-of-the-art high-voltage GaN HEMT and low-voltage silicon MOSFET technologies — offering superior reliability and performance.

2. Features and benefits

- Ultra-low reverse recovery charge
- Simple gate drive (0 V to +10 V or 12 V)
- Robust gate oxide (±20 V capability)
- High gate threshold voltage (+4 V) for very good gate bounce immunity
- · Very low source-drain voltage in reverse conduction mode
- Transient over-voltage capability (800 V)

3. Applications

- Hard and soft switching converters for industrial and datacom power
- Bridgeless totempole PFC
- PV and UPS inverters
- Servo motor drives

4. Quick reference data

Table 1. Qui	ick reference data					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{DS}	drain-source voltage	-55 °C ≤ T _j ≤ 175 °C	-	-	650	V
ID	drain current	V _{GS} = 10 V; T _{mb} = 25 °C; <u>Fig. 2</u>	-	-	34.5	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>	-	-	143	W
Tj	junction temperature		-55	-	175	°C
Static chara	acteristics		I		_	
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C	-	50	60	mΩ
Dynamic ch	naracteristics		· · · · ·		_	
Q _{GD}	gate-drain charge	I _D = 25 A; V _{DS} = 400 V; V _{GS} = 10 V;	-	4	-	nC
Q _{G(tot)}	total gate charge	T _j = 25 °C	-	15	-	nC
Source-dra	in diode		· · · · ·		-	
Qr	recovered charge	I_{S} = 25 A; dI _S /dt = -1000 A/µs; V _{GS} = 0 V; V _{DS} = 400 V; <u>Fig. 14</u>	-	125	-	nC

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5. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	mb	D
2	S	source		
3	D	drain		
mb	S	mounting base; connected to source	TO-247 (SOT429)	G G aaa-028116

6. Ordering information

Type number	Package						
	Name	Description	Version				
GAN063-650WSA		plastic, single-ended through-hole package; 3 leads; 5.45 mm pitch; 20.45 mm x 15.6 mm x 4.95 mm body	SOT429				

7. Marking

Table 4. Marking codes	
Type number	Marking code
GAN063-650WSA	GAN063-650WSA

8. Limiting values

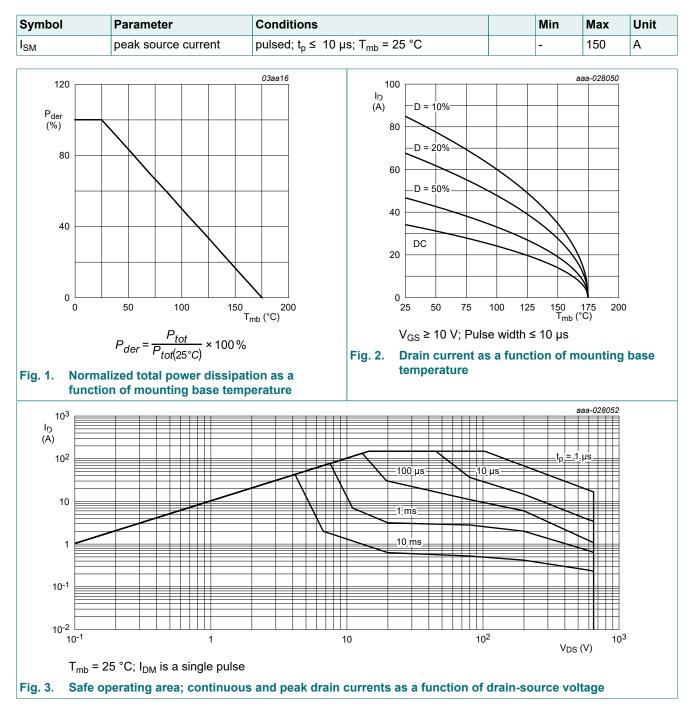
Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{DS}	drain-source voltage	-55 °C ≤ T _j ≤ 175 °C	-	650	V
V _{TDS}	transient drain to source voltage	pulsed; $t_p = 1 \ \mu s$; $\delta_{factor} = 0.01$	-	800	V
V _{GS}	gate-source voltage		-20	20	V
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>	-	143	W
I _D	drain current	V _{GS} = 10 V; T _{mb} = 25 °C; <u>Fig. 2</u>	-	34.5	А
		V _{GS} = 10 V; T _{mb} = 100 °C; <u>Fig. 2</u>	-	24.4	А
I _{DM}	peak drain current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$; Fig. 3	-	150	А
T _{stg}	storage temperature		-55	175	°C
Tj	junction temperature		-55	175	°C
T _{sld(M)}	peak soldering temperature		-	260	°C
Source-drai	n diode	· · ·			
ls	source current	T _{mb} = 25 °C; V _{GS} = 0 V	-	34.5	А

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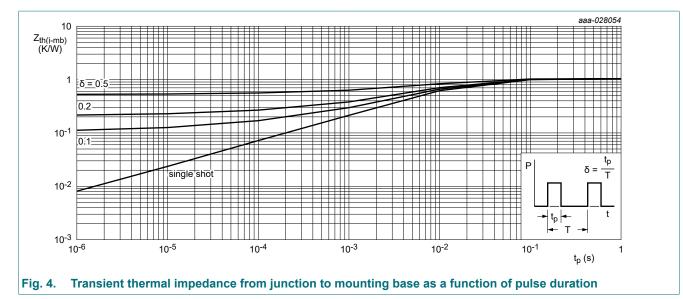
9. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	<u>Fig. 4</u>	-	-	1.05	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	vertical in free air	-	-	40	K/W

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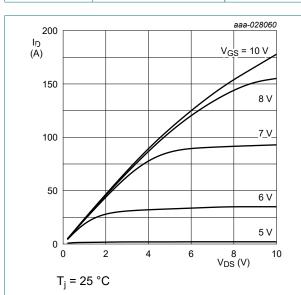
10. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
Static chara	acteristics	· · ·				
V _{GS(th)}	gate-source threshold voltage	I _D = 1 mA; V _{DS} =V _{GS} ; T _j = 25 °C	3.4	3.9	4.5	V
		I _D = 1 mA; V _{DS} =V _{GS} ; T _j = 175 °C; <u>Fig. 9</u>	2.2	-	-	V
		I _D = 1 mA; V _{DS} =V _{GS} ; T _j = -55 °C; <u>Fig. 9</u>	-	-	5.2	V
I _{DSS}	drain leakage current	V _{DS} = 650 V; V _{GS} = 0 V; T _j = 25 °C	-	2	25	μA
		V _{DS} = 650 V; V _{GS} = 0 V; T _j = 175 °C	-	25	-	μA
I _{GSS}	gate leakage current	V _{GS} = -20 V; V _{DS} = 0 V; T _j = 25 °C	-	10	100	nA
		V _{GS} = 20 V; V _{DS} = 0 V; T _j = 25 °C	-	10	100	nA
R _{DSon}	drain-source on-state	V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C	-	50	60	mΩ
	resistance	V _{GS} = 10 V; I _D = 25 A; T _j = 175 °C; Fig. 10	-	120	-	mΩ
R _G	gate resistance	f = 1 MHz	-	2.3	-	Ω
Dynamic ch	aracteristics	· · · ·			-	
Q _{G(tot)}	total gate charge	I _D = 25 A; V _{DS} = 400 V; V _{GS} = 10 V;	-	15	-	nC
Q _{GS}	gate-source charge	T _j = 25 °C	-	6	-	nC
Q _{GD}	gate-drain charge		-	4	-	nC
C _{iss}	input capacitance	V _{DS} = 400 V; V _{GS} = 0 V; f = 1 MHz;	-	1000	-	pF
C _{oss}	output capacitance	T _j = 25 °C; <u>Fig. 11</u>	-	130	-	pF
C _{rss}	reverse transfer capacitance		-	8	-	pF
C _{o(er)}	effective output capacitance, energy related	$0 V \le V_{DS} \le 400 V; V_{GS} = 0 V;$ T _j = 25 °C; <u>Fig. 12</u>	-	190	-	pF
C _{o(tr)}	effective output capacitance, time related	$0 V \le V_{DS} \le 400 V; V_{GS} = 0 V;$ T _j = 25 °C	-	310	-	pF

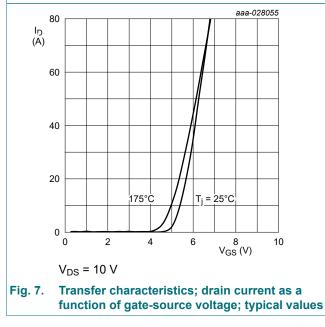
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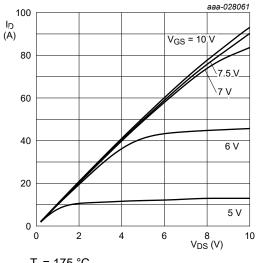
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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
t _{d(on)}	turn-on delay time	V_{DS} = 400 V; R _L = 16 Ω; V _{GS} = 12 V;	-	57	-	ns
t _r	rise time	$R_{G(ext)} = 40 \Omega$	-	10	-	ns
t _{d(off)}	turn-off delay time		-	88	-	ns
t _f	fall time		-	11	-	ns
Q _{oss}	output charge	V _{GS} = 0 V; V _{DS} = 400 V	-	125	-	nC
Source-dra	ain diode					
V _{SD}	source-drain voltage	I_{S} = 25 A; V_{GS} = 0 V; T_{j} = 25 °C; <u>Fig. 13</u>	-	1.9	-	V
		I _S = 12.5 A; V _{GS} = 0 V; T _j = 25 °C	-	1.35	-	V
t _{rr}	reverse recovery time	I _S = 25 A; dI _S /dt = -1000 A/μs;	-	54	-	ns
Q _r	recovered charge	V _{GS} = 0 V; V _{DS} = 400 V; <u>Fig. 14</u>	-	125	-	nC



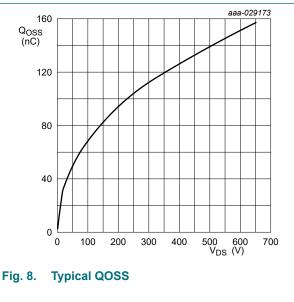






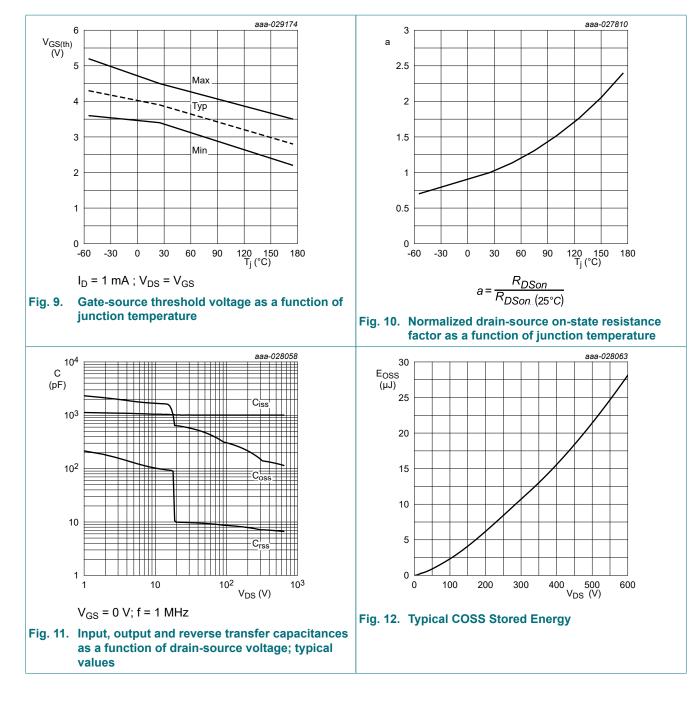






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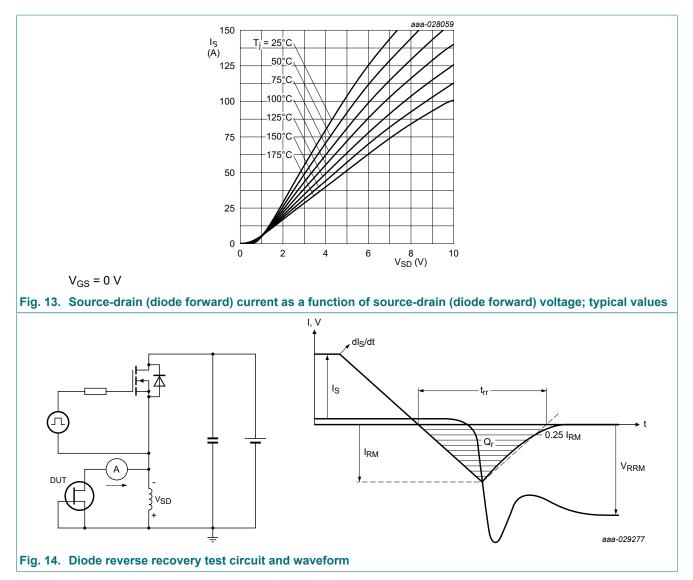
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Product data sheet

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11. Application information

To achieve maximum efficiency and stability when switching high currents, a switching node RC snubber (R_{sn} , C_{sn}) is recommended. For $I_L < 14$ A, a switching-node snubber is not required.

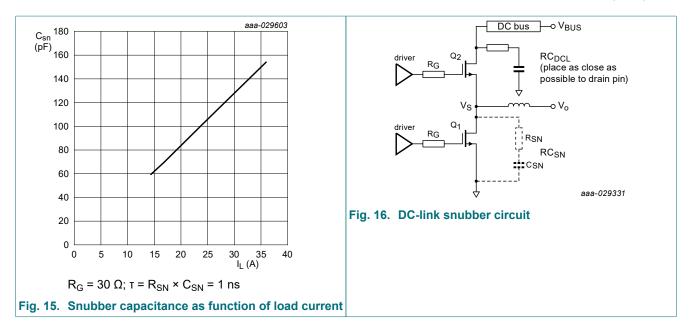
 C_{SN} is taken from the graph.

 R_{SN} should be selected to achieve a time constant of 1 ns; e.g. if C_{SN} = 100 pF, R_{SN} = 1 ns / 100 pF = 10 $\Omega.$

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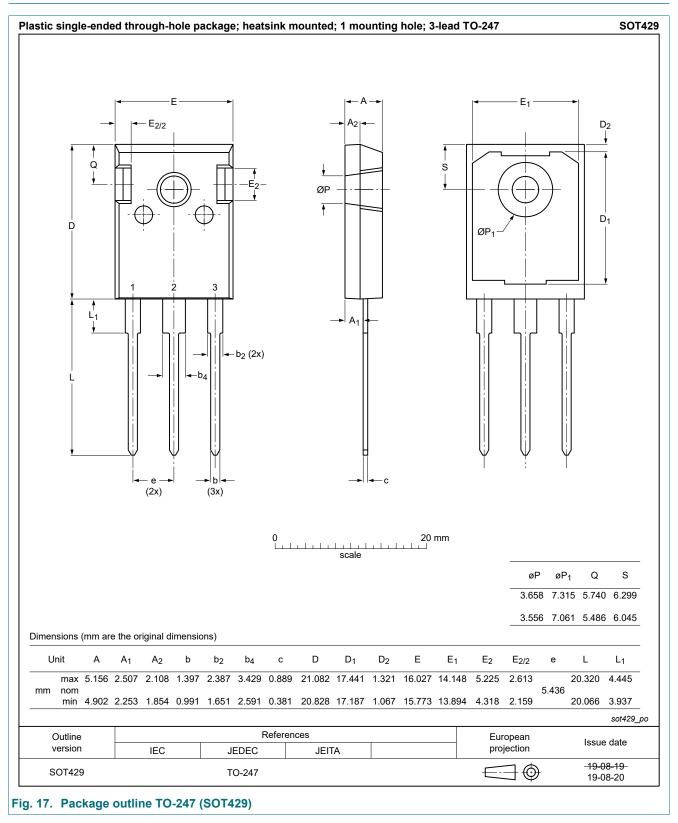


Note: A DC-link snubber is recommended in all cases. Optimal is 20 nF in series with 4 Ω , most easily achieved with parallel combination 10 nF and 8 Ω . This snubber lowers the Q factor of any resonance in the bus. That resonance will act as a load on the high gain amplifier that is the GaN FET and can lead to instability. For very high current, an RC snubber is recommended for the switching node. This will increase switching loss, so this is only recommended at high power levels where the losses are a very small percentage of the total power.

Product data sheet

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12. Package outline



13. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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- [2] The term 'short data sheet' is explained in section "Definitions".
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the internet at <u>https://www.nexperia.com</u>.

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